Silicon Compatible Emerging Materials, Processes, and Technologies for Advanced CMOS and PostCMOS Applications 12

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Sponsoring Divisions:

Published by
The Electrochemical Society
65 South Main Street, Building D
Pennington, NJ 08534-2839, USA
tel 609 737 1902
fax 609 737 2743
www.electrochem.org

ecs transactions ™
Vol. 108, No. 5

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-5862 (online)

ISBN 978-1-60768-945-4 (PDF)

Printed in the United States of America.

ECS Transactions, **Volume 108, Issue 5**
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Table of Contents

Preface *iii*

*(Digital Presentation)*A An Advanced Process Control Scheme for Fin Etching Process in Front-End-of-Line FinFET High Volume Production 3
J. Song, X. Ke, E. N. Zhang, S. Ji, Z. Zhao, C. Zheng, Z. Li, H. Y. Zhang

Dopant Activation Depth Profiling for Highly Doped Si:P By Scanning Spreading Resistance Microscopy (SSRM) and Differential Hall Effect Metrology (DHEM) 9
U. Celano, L. Wouters, A. Franquet, V. Spampinato, P. van der Heide, M. Schaekers, A. Joshi, B. M. Basol

*(Digital Presentation)*A Advanced Process Control of Dual Patterns for FinFET Mass Production 17
X. Ke, F. Li, Z. Zhao, S. Ji, X. Xiao, Z. Li, C. Jiang, H. Zhang

Study on Lifetimes of Plasma Etched Ru Lines 23
J. Q. Su, Y. Kuo

Development Of High Resistivity FD-SOI Substrates for mmWave Applications 31
I. Bertrand, P. Flatresse, G. Besnard, J. M. Bethoux, Z. Chalupa, C. Plantier, M. Rack, M. Nabet, J. P. Raskin, F. Allibert

(Digital Presentation) Characterization and Compression Technology of Real 3D Corner Residue Between Dummy Gate and Formed Fin During an Advanced Inductive Coupled Plasma (ICP) Gate Etch Process in Advanced FinFET 47
X. Xiao, Y. Wang, B. Su, X. Ke, S. Ji, H. Y. Zhang

Formation of Free Hydrogen Gas By Annealing ALD-Al_2O_3/Si Stacked Structure 57
R. Matsumura, N. Fukata

(Digital Presentation) Extending the Application of Capacitively Coupled Plasma Etching Tools to the Front-End-of-Line Fin-Cut Etching Process for FinFET Mass Production 63
Z. Zhao, Z. Chen, X. Ke, F. Li, J. Song, S. Ji, H. Zhang

SiGe Epitaxial Growth on Si Substrate Using Al-Ge Paste 71
S. Suzuki, M. Matsubara, H. Minamiyama, M. Dhamrin, Y. Uraoka

Crystallization Of Tensile Strained n-Type Ge By Continuous Wave Laser Annealing 79
R. H. Saputro, R. Matsumura, N. Fukata

*(Invited)*A Vertical GeSn/Ge Heterostructure Gate-All-Around Nanowire p-MOSFETs 83
Y. Junk, M. Liu, M. Frauenrath, J. M. Hartmann, D. Gruetzmacher, D. Buca, Q. T. Zhao

An Alternate Approach to Backside Thinning: A Doping Selective Silicon Wet Etch 93
J. Bahena, J. Fijal, P. Tyler, J. Taddei, M. Wiemann, M. Figge

Author Index 105